

# MMG100W120XB6T4N

1200V 100A PIM Module

February 2017

Version 1

RoHS Compliant

## PRODUCT FEATURES

- ¶ High level of integration
- ¶ CHIP(Trench+Field Stop IGBT4 and EmCon4 diode)
- ¶ Lo] TJ 10.0861 0 0 10.08 383.88 504.6803 Tm .0019 Tc 0 Tw [(Rect)6.1(ifier+Brak)-9.7(e+l)6.1(n)-1.1(v)-9.7(e)-1.1(rt)6.1(er)]TJ ET 1 i q 1 0 0 1 3

## APPLICATIONS

- ¶ Motion/servo control
- ¶ Inverter and power supplies

$I_{CM}$

=175

100



Unit  
V

Unit  
V  
V  
 $\mu$ A  
mA  
V

Unit

mA

mA

nA

$\mu$ C

nF

pF

ns

ns

ns

ns

ns

ns

Unit  
K  
K

Unit

V

Nm  
g



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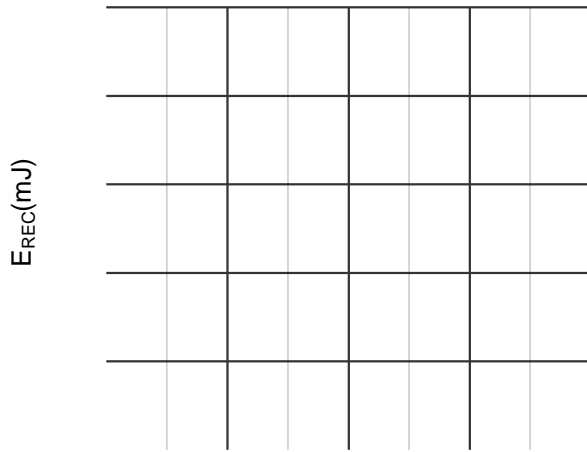


Figure 9. Switching Energy vs Forward Current Diode-inverter

$Z_{thjc}(K/W)$

Figure 10. Transient Thermal Impedance of Diode and IGBT-inverter

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Figure 15. Collector Current vs Case temperature  
IGBT -inverter

Figure 16. Forward current vs Case temperature  
Diode -inverter



